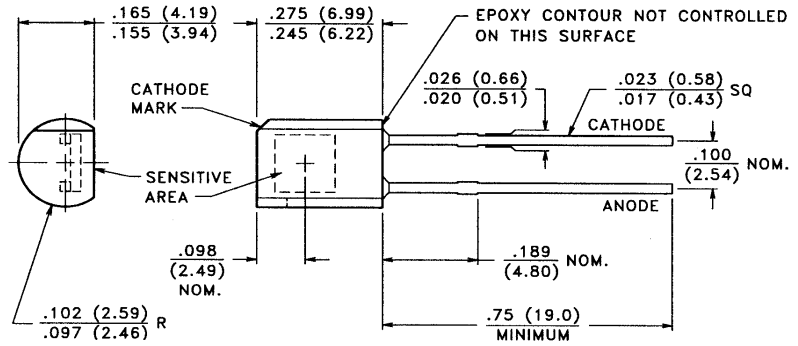




**PACKAGE DIMENSIONS** inch (mm)



CASE 61 TO-92 TYPE (FLAT LENS)  
CHIP ACTIVE AREA: .011 in<sup>2</sup> (7.41 mm<sup>2</sup>)

**PRODUCT DESCRIPTION**

Large area planar silicon photodiode in a waterclear, cast epoxy sidelooker, similar in outline to the TO-92 package. These diodes exhibit low dark current under reverse bias and fast speed of response.

**ABSOLUTE MAXIMUM RATINGS**

Storage Temperature: -40°C to 100°C  
Operating Temperature: -40°C to 100°C

**RoHS Compliant**



**ELECTRO-OPTICAL CHARACTERISTICS @ 25°C**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTD206KH			UNITS
			Min.	Typ.	Max.	
I <sub>SC</sub>	Short Circuit Current	1000 Lux, 2856 K	50	80		μA
TC I <sub>SC</sub>	I <sub>SC</sub> Temperature Coefficient	2856 K		.20		%/°C
V <sub>OC</sub>	Open Circuit Voltage	940 nm, H = 0.5 mW/cm <sup>2</sup>	310	365		mV
TC V <sub>OC</sub>	V <sub>OC</sub> Temperature Coefficient	2856 K		-2.6		mV/°C
I <sub>D</sub>	Dark Current	H = 0, V <sub>R</sub> = 10 V		2	30	nA
C <sub>J</sub>	Junction Capacitance	H = 0, V <sub>R</sub> = 0 V, 1 MHz		72		pF
t <sub>R</sub> /t <sub>F</sub>	Rise/Fall Time @ RL = 50Ω	V <sub>R</sub> = 5 V, 850 nm		20		nsec
S <sub>R</sub>	Sensitivity	@ Peak		0.6		A/W
λ <sub>range</sub>	Spectral Application Range		400		1100	nm
λ <sub>p</sub>	Spectral Response - Peak			925		nm
V <sub>BR</sub>	Breakdown Voltage		20	50		V
θ <sub>1/2</sub>	Angular Resp.-50% Resp. Pt.			+60		Degrees